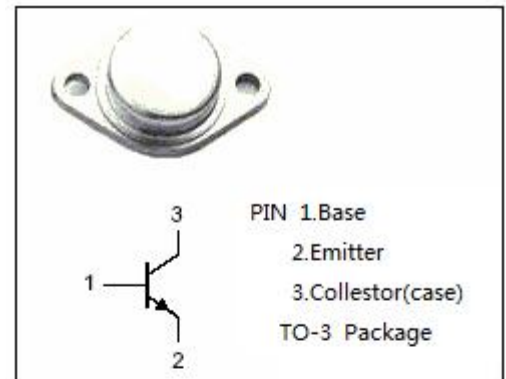


**isc Silicon NPN Power Transistor**
**BD366**
**DESCRIPTION**

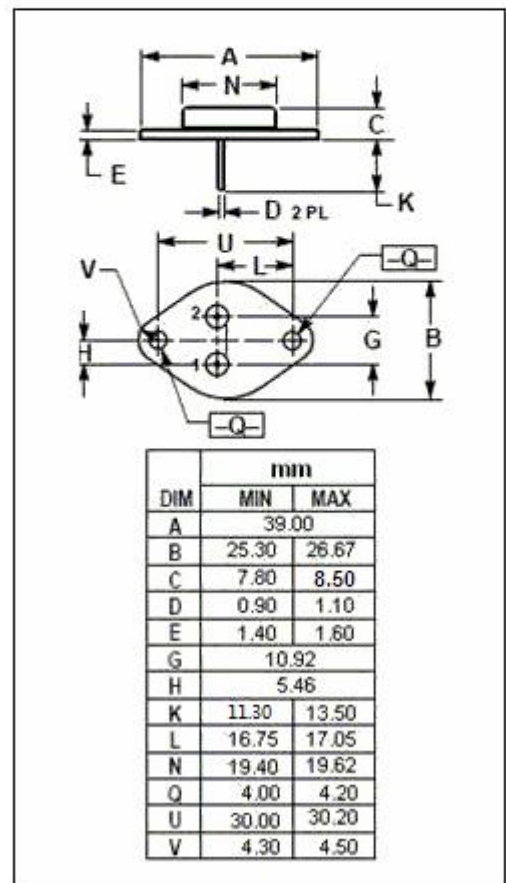
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 60V(\text{Min})$
- Excellent Safe Operating Area
- Complement to Type BD367
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for linear amplifiers, series pass regulators, and inductive switching applications.


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	25	A
$I_B$	Base Current-Continuous	5	A
$P_C$	Collector Power Dissipation@ $T_c=25^\circ\text{C}$	200	W
$T_J$	Junction Temperature	175	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~175	$^\circ\text{C}$


**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.875	$^\circ\text{C/W}$

**isc Silicon NPN Power Transistor**
**BD366**

## ELECTRICAL CHARACTERISTICS

**T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =30mA ; I <sub>B</sub> =0	60			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10A; I <sub>B</sub> =1A			1.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =20A; I <sub>B</sub> =2A			1.5	V
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> =10A; I <sub>B</sub> =1A			1.5	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> =20A; I <sub>B</sub> =2A			2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> =60V; I <sub>E</sub> =0			0.1	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 60V; I <sub>B</sub> = 0			0.5	mA
I <sub>EBO</sub>	Emitter Cutoff current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	40			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> =15A ; V <sub>CE</sub> =5V	25		100	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> =25A ; V <sub>CE</sub> =5V	5			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> =1A;V <sub>CE</sub> =10V;f=1.0MHz	4.0			MHz

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